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## Contents

<b>Preface</b> .....	V
<b>Contributors</b> .....	XVII
<b>1 Strained-Si CMOS Technology</b>	
<i>S. Takagi</i> .....	1
1.1 Introduction .....	1
1.2 Impact of Mobility Enhancement on Current Drive of Short-Channel MOSFETs .....	2
1.3 Physical Mechanism of Mobility Enhancement in Strained-Si n- and p-Channel MOSFETs .....	3
1.3.1 Physical Origin of Mobility Enhancement in n-Channel MOSFETs .....	3
1.3.2 Physical Origin of Mobility Enhancement in p-Channel MOSFETs .....	7
1.4 Implementation of Strain into MOSFETs .....	11
1.4.1 Global Strain Technology .....	11
1.4.2 Local Strain Technology .....	13
1.5 Conclusions .....	14
References .....	15
<b>2 High Current Drivability MOSFET Fabricated on Si(110) Surface</b>	
<i>A. Teramoto, T. Ohmi</i> .....	21
2.1 Introduction .....	21
2.2 Experimental .....	22
2.3 Results and Discussions .....	24
2.3.1 MOSFET Characteristics on the Si(110) Surface .....	24
2.3.2 Suppression of Surface Micro-roughness .....	29
2.4 Conclusions .....	38
References .....	39

**3 Advanced High-Mobility Semiconductor-on-Insulator****Materials**

<i>B. Ghyselen, I. Cayrefourcq, M. Kennard, F. Letertre,</i>	
<i>T. Akatsu, G. Celler, C. Mazure</i> .....	43
3.1 Introduction .....	43
3.2 Crystalline Orientation Effects .....	44
3.2.1 Silicon Crystalline Orientations for Bulk Substrates .....	44
3.2.2 Silicon Crystalline Orientations for SOI Substrates .....	45
3.2.3 Perspectives for Crystalline Orientations in SOI Substrates .....	47
3.3 Strained Si on Insulator Wafers .....	48
3.3.1 Introduction to Strained Si on Insulator Wafers .....	48
3.3.2 “Local Strain” .....	48
3.3.3 “Global Strain” .....	49
3.3.4 Two Main Approaches to “Global Strain On Insulator”: SGOI Vs. sSOI .....	51
3.3.5 Different Routes Towards SGOI .....	52
3.3.6 SGOI Material Concept Validation Through Device Demonstrations .....	55
3.3.7 sSOI Substrates: Ge-free Strained Si On Insulator Substrates .....	57
3.3.8 Thick sSOI Substrates .....	59
3.3.9 Device Results on sSOI .....	60
3.4 Germanium On Insulator Substrates .....	60
3.4.1 Introduction to GeOI Substrates .....	60
3.4.2 GeOI Substrates Manufacturing Routes .....	61
3.4.3 Examples of GeOI Substrates Validations at Device Level .....	64
3.5 Long Term Perspectives .....	65
3.6 Conclusions .....	66
References .....	67

**4 Passivation and Characterization of Germanium Surfaces**

<i>S.R. Amy, Y.J. Chabal</i> .....	73
4.1 Introduction .....	73
4.2 Experimental Methodology .....	74
4.2.1 X-ray and UV Photoemission Spectroscopy .....	74
4.2.2 Fourier Transform Infrared Spectroscopy .....	75
4.2.3 Scanning Tunneling Microscopy .....	76
4.3 Clean Ge Surfaces .....	76
4.4 Oxidation of Ge Surfaces .....	76
4.5 Hydrogenation of Germanium Surfaces .....	83
4.5.1 Hydrogenation in Ultra High Vacuum .....	83
4.5.2 Wet Chemical Treatment of Flat Single Crystal Germanium Surfaces .....	83

4.5.3	Electrochemistry on Flat Single Crystal Germanium Surfaces .....	89
4.5.4	Electrochemistry on Porous Germanium Substrate .....	91
4.6	Nitridation and Oxynitridation of Germanium Surfaces .....	93
4.7	Sulfur Passivation of Germanium Surfaces .....	97
4.8	Chlorine Passivation of Germanium Surfaces .....	99
4.9	Organic Molecules as Passivating Agent of Germanium Surfaces .....	101
4.10	Conclusions .....	104
	References .....	111
<b>5 Interface Engineering for High-<math>k</math> Ge MOSFETs</b>		
	<i>S.J. Lee, C. Zhu, D.L. Kwong</i> .....	115
5.1	Introduction .....	115
5.2	Germanium Oxide and High- $k$ /Ge Interface .....	116
5.3	Surface Nitridation .....	122
5.3.1	Physical Characterization .....	124
5.3.2	MOS Capacitor Characteristics .....	126
5.3.3	MOSFET Performance .....	127
5.4	Surface Silicon Passivation .....	128
5.4.1	Physical Characterization .....	128
5.4.2	MOS Capacitors and Thermal Stability .....	130
5.4.3	MOSFET Performance .....	132
5.4.4	BTI and Charge Trapping .....	133
5.5	Plasma-PH <sub>3</sub> and AlN Surface Passivation .....	135
5.6	Conclusion .....	137
	References .....	137
<b>6 Effect of Surface Nitridation on the Electrical Characteristics of Germanium High-<math>\kappa</math>/Metal Gate Metal-Oxide-Semiconductor Devices</b>		
	<i>D.Q. Kelly, J.J.-H. Chen, S. Guha, S.K. Banerjee</i> .....	139
6.1	Introduction .....	139
6.2	Germanium Surface Cleaning .....	141
6.3	Surface Pretreatment with NH <sub>3</sub> (Surface Nitridation) .....	144
6.4	Effect of Surface Nitridation on the Electrical Characteristics of Germanium MOS Capacitors .....	147
6.4.1	Al <sub>2</sub> O <sub>3</sub> /Ge and HfO <sub>2</sub> /Ge Capacitor Fabrication .....	149
6.4.2	Electrical Characterization of Al/Al <sub>2</sub> O <sub>3</sub> /Ge Capacitors ....	152
6.4.3	Electrical Characterization of Al/HfO <sub>2</sub> /Ge and W/HfO <sub>2</sub> /Ge Capacitors .....	155
6.5	Conclusions .....	159
	References .....	160

## 7 Modeling of Growth of High- $k$ Oxides on Semiconductors

<i>C.J. Först, C.A. Ashman, K. Schwarz, P.E. Blöchl</i> .....	165
7.1 Introduction .....	165
7.2 Computational Approach .....	166
7.3 The Chemistry of the Substrate .....	167
7.4 Metal Adsorption on Si(001) .....	168
7.5 Interface of SrTiO <sub>3</sub> and Si(001) .....	174
7.6 Band Offset Engineering .....	175
7.7 Conclusions .....	178
References .....	178

## 8 Physical, Chemical, and Electrical Characterization of High- $\kappa$ Dielectrics on Ge and GaAs

<i>S. Spiga, C. Wiemer, G. Scarel, G. Sequini, M. Fanciulli, A. Zenkevich, Yu. Lebedinskii</i> .....	181
8.1 Introduction .....	181
8.2 Experimental Methodology: ALD Deposition and Characterization Techniques .....	183
8.3 Structural and Chemical Properties .....	186
8.3.1 HfO <sub>2</sub> Films Deposited by ALD on Ge and GaAs Using Various Precursor Combinations .....	186
8.3.2 Local Epitaxy of HfO <sub>2</sub> Films Grown by ALD on Ge(001) and GaAs(001) .....	189
8.3.3 Lu <sub>2</sub> O <sub>3</sub> Films Deposited by ALD on Ge and GaAs .....	192
8.4 Electrical Properties of High- $\kappa$ Dielectrics on Ge and GaAs .....	194
8.4.1 Electrical Properties of High- $\kappa$ Dielectrics Deposited on Ge: HfO <sub>2</sub> , Al <sub>2</sub> O <sub>3</sub> , and Lu <sub>2</sub> O <sub>3</sub> .....	194
8.4.2 Electrical Properties of High- $\kappa$ Dielectrics Deposited on GaAs .....	197
8.5 Band Offset of High- $\kappa$ Dielectrics Deposited on Ge and GaAs .....	198
8.6 Conclusions .....	201
References .....	202

## 9 Point Defects in Stacks of High- $\kappa$ Metal Oxides on Ge: Contrast with the Si Case

<i>A. Stesmans, V.V. Afanas'ev</i> .....	211
9.1 Introduction .....	211
9.1.1 Previous ESR Results .....	215
9.2 Experimental Methodology and Samples .....	216
9.2.1 ESR Spectroscopy .....	216
9.2.2 Electrical Analysis .....	217
9.2.3 Samples .....	217

9.3	Experimental Results .....	217
9.3.1	Electrical Analysis .....	217
9.3.2	ESR Measurements .....	220
9.4	Discussion .....	223
9.5	Conclusions .....	225
	References .....	226
 <b>10 High <math>\kappa</math> Gate Dielectrics for Compound Semiconductors</b>		
	<i>J. Kwo, M. Hong</i> .....	229
10.1	Introduction .....	229
10.2	High $\kappa$ Gate Dielectrics for GaAs and its Related Compounds: Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> ) Approach .....	232
10.3	Thermodynamic Stability of Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> )/GaAs Interface at High Temperatures [26] .....	236
10.4	Single Crystal Gd <sub>2</sub> O <sub>3</sub> on GaAs and Interfaces .....	239
10.5	GaAs MOSFETs .....	242
10.5.1	Enhancement-Mode with Inversion .....	242
10.5.2	Depletion-Mode MOSFET and Power Devices .....	243
10.6	High $\kappa$ Gate Dielectrics for GaAs and its Related Compounds: ALD Al <sub>2</sub> O <sub>3</sub> Approach and its Mechanism of Unpinning the Fermi Level [31] .....	246
10.7	GaN Passivation .....	250
10.8	Conclusion .....	253
	References .....	254
 <b>11 Interface Properties of High-<math>k</math> Dielectrics on Germanium</b>		
	<i>A. Toriumi, K. Kita, M. Toyama, H. Nomura</i> .....	257
11.1	Introduction .....	257
11.2	Experimental .....	258
11.3	Results and Discussion .....	259
11.3.1	Effect of Hf Metal Pre-deposition Prior to HfO <sub>2</sub> Deposition [5] .....	259
11.3.2	Effects of Ge Surface Orientation .....	261
11.3.3	Y <sub>2</sub> O <sub>3</sub> and HfO <sub>2</sub> on (100) Ge [9,10] .....	262
11.4	Conclusion .....	266
	References .....	267
 <b>12 A Theoretical View on the Dielectric Properties of Crystalline and Amorphous High-<math>\kappa</math> Materials and Films</b>		
	<i>V. Fiorentini, P. Delugas, A. Filippetti</i> .....	269
12.1	Introduction .....	269
12.1.1	Linear Response Theory and Dielectric Properties .....	270
12.2	A Crystal Selection: Dioxides, Sesquioxides, Aluminates .....	273
12.2.1	Multiphase and Epitaxial Transition-Metal Dioxides .....	273

12.2.2 Sesquioxides: Lutetia, Lanthana, and the Hex–Bix Difference .....	274
12.2.3 Rare-Earth and Transition-Metal Aluminates .....	277
12.3 Amorphous and Alloyed Systems: Silica, Aluminates, Silicates .....	280
12.3.1 A Pioneering Study of Silica .....	280
12.3.2 Amorphous Zirconia .....	281
12.3.3 Conservation of Permittivity in Amorphous Lanthanide Aluminates? .....	283
12.3.4 Dielectric Enhancement in Aluminate Alloys .....	285
12.3.5 Models vs. Ab Initio Predictions in Transition-Metal Silicates .....	286
12.4 Local Microscopic Screening in Ultrathin Films .....	287
12.5 Conclusions .....	289
References .....	290
 <b>13 Germanium Nanodevices and Technology</b>	
<i>C.O. Chui, K.C. Saraswat</i> .....	293
13.1 Introduction .....	293
13.2 Challenges to Scaling Conventional CMOS .....	293
13.3 Why High Mobility Channel? .....	295
13.4 Which High Mobility Channel Material? .....	295
13.5 Heteroepitaxial Ge Growth on Si .....	297
13.6 Nanoscale Gate Stacks on Germanium .....	300
13.6.1 Grown Germanium Oxynitride Dielectrics .....	300
13.6.2 Deposited High-Permittivity Dielectrics .....	300
13.7 Shallow Source–Drain Junctions .....	303
13.7.1 Ion Implantation Doping .....	304
13.7.2 Solid Source Diffusion Doping .....	305
13.8 Metal-Gated Germanium MOSFET Processes .....	306
13.8.1 The Sub-400°C Conventional P-MOSFET Process .....	306
13.8.2 The Simple Self-Aligned Gate-Last n-MOSFET Process .....	307
13.9 Conclusions .....	310
References .....	311
 <b>14 Opportunities and Challenges of Germanium Channel MOSFETs</b>	
<i>H. Shang, E.P. Gusev, M.M. Frank, J.O. Chu, S. Bedell, M. Gribelyuk, J.A. Ott, X. Wang K.W. Guarini, M. Jeong</i> .....	315
14.1 Introduction .....	315
14.2 Ge Surface Channel MOSFETs .....	316
14.2.1 Gate Dielectric .....	316
14.2.2 Ge Surface Preparation .....	316
14.2.3 Dopant Diffusion and Junction Leakage .....	317

14.3 Strained Ge Buried Channel MOSFETs .....	319
14.3.1 Device Design and Scaling Prospect for Strained Ge Buried Channel Devices .....	320
14.3.2 Material Growth and Thermal Stability .....	321
14.3.3 Gate Stack for s-Ge MOSFETs .....	322
14.3.4 Integration of s-Ge Channel MOSFETs .....	323
14.4 Conclusions .....	329
References .....	330
 <b>15 Germanium Deep-Submicron p-FET and n-FET Devices, Fabricated on Germanium-On-Insulator Substrates</b>	
<i>M. Meuris, B. De Jaeger, J. Van Steenberghe, R. Bonzom, M. Caymax, M. Houssa, B. Kaczer, F. Leys, K. Martens, K. Opsomer, A.M. Pourghaderi, A. Satta, E. Simoen, V. Terzieva, E. Van Moorhem, G. Winderickx, R. Loo, T. Clarysse, T. Conard, A. Delabie, D. Hellin, T. Janssens, B. Onsia, S. Sioncke, P.W. Mertens, J. Snow, S. Van Elshocht, W. Vandervorst, P. Zimmerman, D. Brunco, G. Raskin, F. Letertre, T. Akatsu, T. Billon, M. Heyns</i> .....	333
15.1 Introduction .....	333
15.2 Ge Gate Stack Capacitor .....	334
15.3 Dopant Activation in Germanium .....	336
15.4 GeOI Substrates .....	337
15.5 Conclusions .....	338
References .....	339
 <b>16 Processing and Characterization of III–V Compound Semiconductor MOSFETs Using Atomic Layer Deposited Gate Dielectrics</b>	
<i>P.D. Ye, G.D. Wilk, M.M. Frank</i> .....	341
16.1 Introduction .....	341
16.2 Materials Structure and Composition .....	343
16.3 Electrical Characterization of ALD Al <sub>2</sub> O <sub>3</sub> on GaAs .....	346
16.4 GaAs MOSFET Fabrication and Characterization .....	349
16.5 InGaAs MOSFET Fabrication and Characterization .....	352
16.6 GaN MOS-HEMT Fabrication and Characterization .....	353
16.7 Conclusions .....	356
References .....	358
 <b>17 Fabrication of MBE High-<math>\kappa</math> Mosfets in a Standard CMOS Flow</b>	
<i>L. Pantisano, T. Conard, T. Scram, W. Deweerdt, S. De Gendt, M. Heyns, Z.M. Rittersma, C. Marchiori, M. Sousa, J. Fompeyrine, J.-P. Locquet</i> .....	363
17.1 Introduction .....	363
17.2 Device Fabrication .....	364
17.2.1 TEM Pictures and Salient Features .....	364

17.3 Device Characterization .....	365
17.3.1 Large Area Capacitors .....	366
17.3.2 Low Leakage in LHO Devices .....	366
17.3.3 Long-Channel MOSFET with $\text{HfO}_2$ as Gate Dielectric .....	367
17.3.4 Long-Channel MOSFET with LHO as Gate Dielectric .....	369
17.3.5 Performance Comparison of MBE Materials With ALD in the ASAP Flow .....	371
17.3.6 Threshold Voltage Instability .....	372
17.4 Conclusions .....	372
References .....	374
<b>Index</b> .....	375



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